

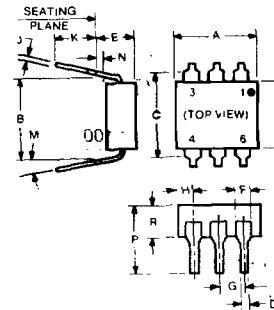
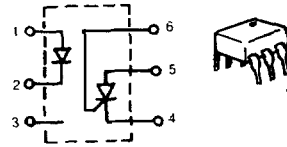
H11M3, H11M4

Optoisolator GaAlAs Infrared Emitting Diode and Light Activated SCR

The H11M3 and H11M4 contain a gallium-aluminum-arsenide, infrared emitting diode coupled to a unique high voltage silicon controlled rectifier within a dual in-line package. These devices are optimized for high performance and long life. They are especially suited for the control of industrial AC power lines from low voltage logic integrated circuitry. These devices are also available in surface-mount packaging.

FEATURES

- High blocking voltage, 600 V minimum
- High isolation voltage, 3750 Vrms minimum (steady state)
- High efficiency, low degradation, liquid epitaxial IRED
- Logic compatible drive current, 7 mA at 1.5 V maximum
- Unique, high performance glass dielectric construction



absolute maximum ratings: (25°C)

INFRARED EMITTING DIODE		
Power Dissipation	*100	milliWatts
Forward Current (Continuous)	60	milliAmpere
Forward Current (Peak) (Pulse width 10 μsec Duty Cycle 1%)	1	Ampere
Reverse Voltage	6	volts

*Derate 1.33mW/°C above 25°C ambient.

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	8.28	9.89	.33	.39	1
B	7.62 REF		.30 REF		
C		8.64		.34	2
D	4.06	5.08	0.16	0.20	
E		5.08		.20	3
F	1.01	1.78	.40	.071	
G	2.28	2.80	.90	.111	4
H		2.16		.85	
I	2.01	.76	.08	.312	
K	2.54		.10		
M		15		.59	
N	3.81		.15		
P		9.53		.375	
R	2.92	1.27	.115	.15	
S	9.10	8.86	.36	.35	

- NOTES
 1. INSTALLED POSITION LEAD CENTERS
 2. OVERALL INSTALLED DIMENSION
 3. THESE MEASUREMENTS ARE MADE FROM THE SEATING PLANE
 4. FOUR PLACES

PHOTO-SCR		
Peak Forward Voltage	600	Volts
RMS Forward Current	300	milliAmperes
Peak On-State Current (1 cycle surge, 10 msec)	3	Amperes
Peak Reverse Gate Voltage	5	Volts
Power Dissipation (25°C Ambient)	**400	milliWatts

**Derate 5.3 mW/°C above 25°C ambient.

TOTAL DEVICE	
Storage Temperature	-55°C to +150°C
Operating Temperature	-55 to +100°C
Lead Soldering Time (at 260°C)	10 seconds
Surge Isolation Voltage (Input to Output)	5656 V _{tp2ak} , 4000 V _{VRMS}
Steady-State Isolation Voltage (Input to Output)	5300 V _{tp2ak} , 3750 V _{VRMS}

Covered under U.L. component recognition program, reference file E51868

H11M3, H11M4

individual electrical characteristics (25°C) (unless otherwise indicated)

EMITTER	SYMBOL	TYP.	MAX.	UNITS
Forward Voltage ($I_f = 10 \text{ mA}$)	V_f	1.3	1.65	V
Reverse Current ($V_R = 5\text{V}$)	I_R	—	10	μA
Capacitance ($V_{AK} = 0\text{V}$, $F = 1 \text{ MHz}$)	C_j	50		pF

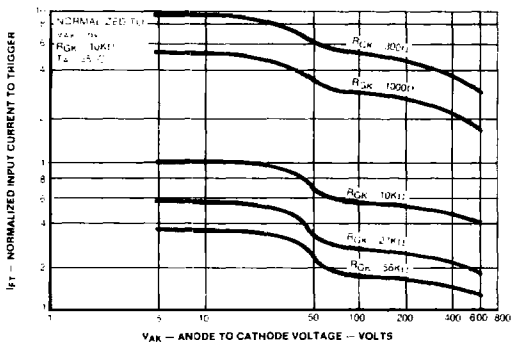
DETECTOR	SYMBOL	MIN.	TYP.	MAX.	UNITS
Off-State Voltage ($R_{GK} = 10\text{K}\Omega$, $I_D = 100\mu\text{A}$, $T_A = 100^\circ\text{C}$)	V_{DM}	600			V
Reverse Voltage ($R_{GK} = 10\text{K}\Omega$, $I_R = 100\mu\text{A}$, $T_A = 100^\circ\text{C}$)	V_{RM}	600			V
On-State Voltage ($I_{TM} = 300\text{mA}$)	V_{TM}	—		1.6	V
Off-State Current ($R_{GK} = 10\text{K}\Omega$, $V_{DM} = 600\text{V}$, $T_A = 100^\circ\text{C}$) ($T_A = 25^\circ\text{C}$)	I_{DM}	—		100 400	μA nA
Reverse Current ($R_{GK} = 10\text{K}\Omega$, $V_{RM} = 600\text{V}$, $T_A = 100^\circ\text{C}$) ($T_A = 25^\circ\text{C}$)	I_{RM}	—		100 400	μA nA
Critical Rate-of-Rise of Off-State Voltage ($V_{AK} = 600\text{V}$, $R_{GK} = 10\text{K}\Omega$)	dv/dt		25		V/ μsec
Holding Current ($R_{GK} = 10\text{K}\Omega$)	I_H			2	mA

coupled electrical characteristics (25°C)

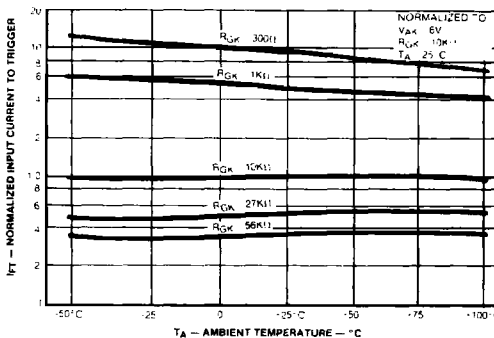
COUPLED	SYMBOL	MIN.	TYP.	MAX.	UNITS
Input Current to Trigger ($V_{AK} = 6\text{V}$, $R_{GK} = 10\text{K}\Omega$)	I_{FI}			10 20	mA mA
Input Current to Trigger ($V_{AK} = 6\text{V}$, $R_{GK} = 27\text{K}\Omega$)	I_{FI}			7 15	mA mA
Isolation Resistance (Input to Output) ($V_{IO} = 500\text{V}$)	r_{io}	100			G Ω
Isolation Capacitance (Input to Output) ($V_{IO} = 0\text{V}$, $F = 1 \text{ MHz}$)	c_{io}			2	pF
Isolation dv/dt Immunity (Input to Output) See Figure 10			500		V/ μsec

Tests of input to output isolation voltage, isolation resistance, and isolation capacitance are performed with the input terminals (pins 1, 2 & 3) shorted together and the output terminals (pins 4, 5 & 6) shorted together.

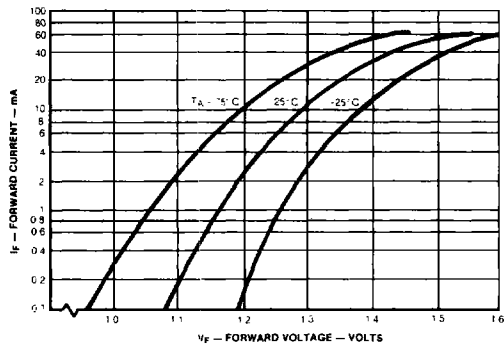
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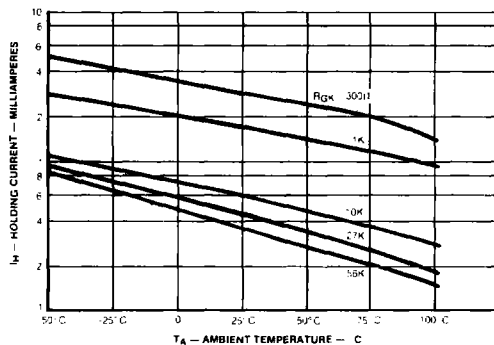
1. INPUT CURRENT TO TRIGGER VS. ANODE TO CATHODE VOLTAGE



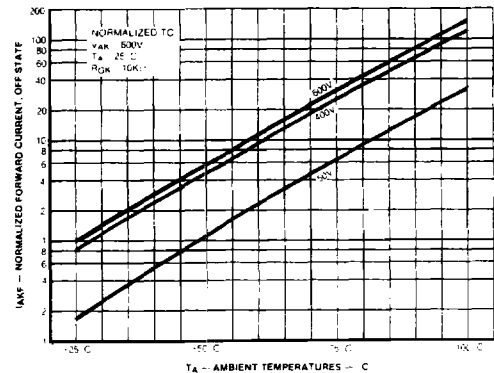
2. INPUT CURRENT TO TRIGGER VS. TEMPERATURE



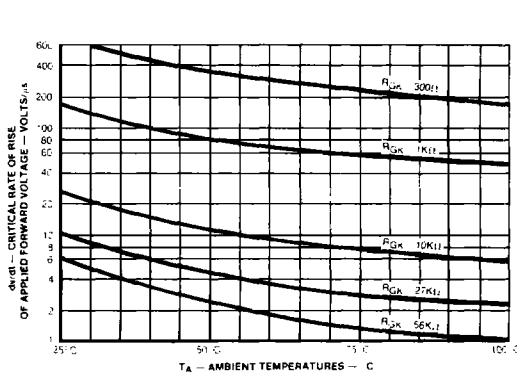
3. INPUT VOLTAGE VS. INPUT CURRENT



4. HOLDING CURRENT VS. TEMPERATURE

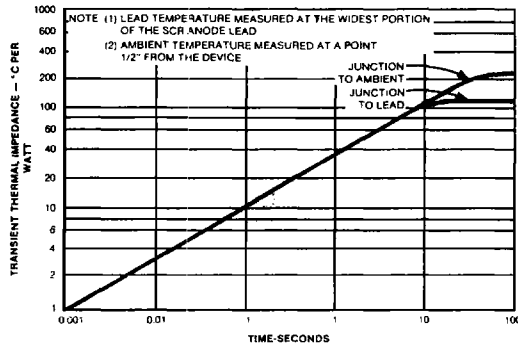


5. OFF-STATE LEAKAGE VS. TEMPERATURE

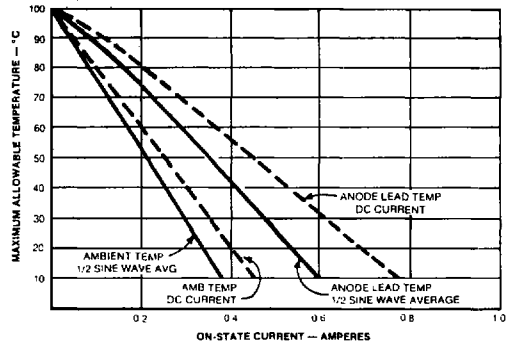


6. dv/dt VS. TEMPERATURE

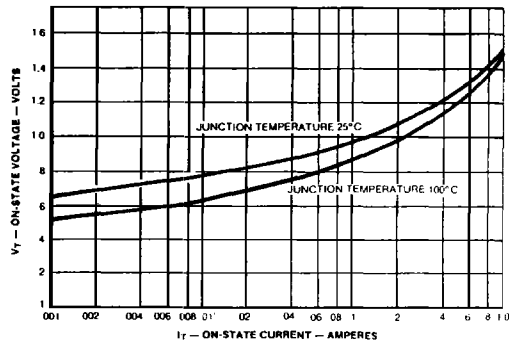
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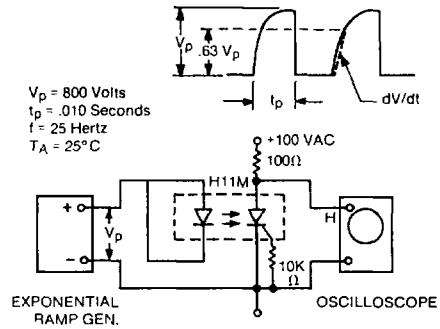
7. MAXIMUM TRANSIENT THERMAL IMPEDANCE



8. ON-STATE CURRENT VS. MAXIMUM ALLOWABLE TEMPERATURE



9. ON-STATE CHARACTERISTICS



10. ISOLATION dv/dt IMMUNITY TEST CIRCUIT